

MMBTA55

PNP EPITAXIAL SILICON TRANSISTOR

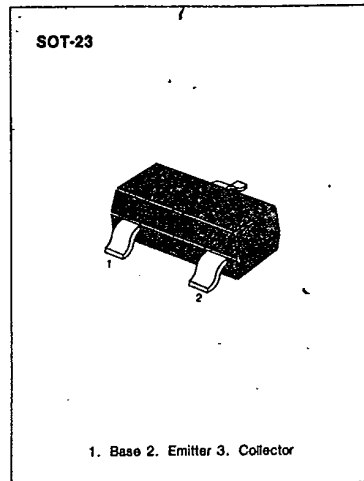
T-29-19

DRIVER TRANSISTOR

ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-60	V
Collector-Emitter Voltage	V _{CE0}	-60	V
Emitter-Base Voltage	V _{EB0}	-4	V
Collector Current	I _c	-500	mA
Collector Dissipation	P _c	350	mW
Storage Temperature	T _{stg}	150	°C
Thermal Resistance Junction to Ambient	R _{th(j-a)}	357	°C/W

• Refer to MPSA55 for graphs



ELECTRICAL CHARACTERISTICS (T_a = 25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
* Collector-Emitter Breakdown Voltage	BV _{CEO}	I _c = -1mA, I _b = 0	-60		V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E = -100μA, I _C = 0	-4		V
Collector Cutoff Current	I _{CB0}	V _{CB} = -60V, I _E = 0		-0.1	μA
Collector Cutoff Current	I _{CE0}	V _{CE} = -80V, I _b = 0		-0.1	μA
DC Current Gain	h _{FE}	V _{CE} = -1V, I _c = -10mA	50		
		V _{CE} = -1V, I _c = -100mA	50		
Collector-Emitter Saturation Voltage	V _{CE (sat)}	I _c = -100mA, I _b = -10mA		-0.25	V
Base-Emitter On Voltage	V _{BE (on)}	V _{CE} = -1V, I _c = -100mA		-1.2	V
Current Gain-Bandwidth Product	f _T	V _{CE} = -1V, I _c = -100mA, f = 100MHz	50		MHz

* Pulse Test: PWS ≤ 300μs, Duty Cycle ≤ 2%

Marking

